

# EE115A Analog Circuits

## Homework 4

Due date: 11/4/2025

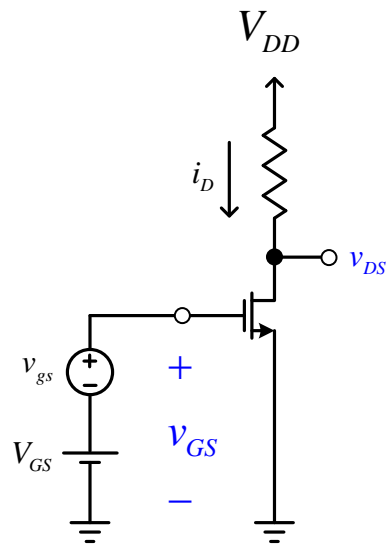
**Note:**

- Please provide enough calculation process to get full marks.
- Please submit your homework to Gradescope (code **J62G3D**) in PDF version.
- It's highly recommended to write every exercise on a single sheet of page.
- Late submissions will have points deducted according to the penalty policy.
- Please use English only to complete the assignment, solutions in Chinese are not allowed.
- Plagiarizer will get zero points.
- The full score of this assignment is 100 points.

### Exercise 1. (20pt)

Consider the MOSFET amplifier of **Fig.P1** for the case  $V_t = 0.4 \text{ V}$ ,  $k_n = 10 \text{ mA/V}^2$ ,  $V_{GS} = 0.6 \text{ V}$ ,  $V_{DD} = 1.8 \text{ V}$ , and  $R_D = 6.8 \text{ k}\Omega$ .

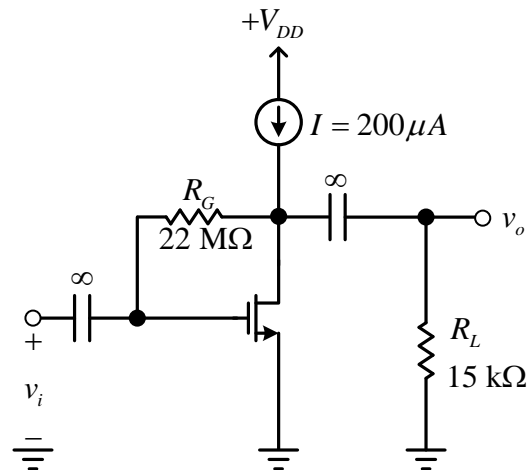
- (a) Find the dc quantities  $I_D$  and  $V_{DS}$
- (b) Calculate the value of  $g_m$  at the bias point.
- (c) Calculate the value of the voltage gain.
- (d) If the MOSFET has  $\lambda = 0.2 \text{ V}^{-1}$ , find  $r_o$ , at the bias point and calculate the voltage gain.



**Fig.P1**

## Exercise 2. (20pt)

In the circuit of **Fig.P2**, the NMOS transistor has  $|V_t| = 0.8 \text{ V}$  and  $V_A = 20 \text{ V}$  and operates with  $V_D = 1 \text{ V}$ . What is the voltage gain  $v_o/v_i$ ? What do  $V_D$  and the gain become for  $I$  increased to  $1 \text{ mA}$ ?



**Fig.P2**

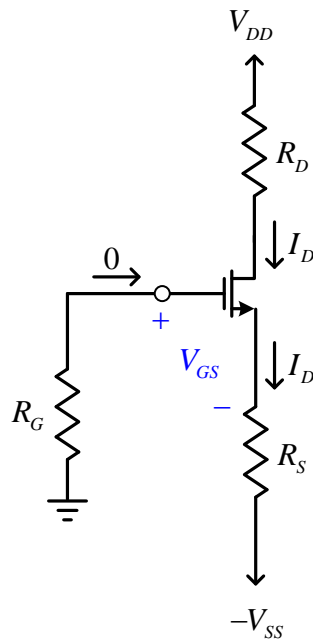
### Exercise 3. (20pt)

A CS amplifier utilizes a MOSFET with  $\mu_n C_{ox} = 400 \mu\text{A}/\text{V}^2$  and  $WL = 10$ . It is biased at  $I_D = 0.5 \text{ mA}$  and uses  $R_D = 10 \text{ k}\Omega$ . Find  $R_{in}$ ,  $A_{vo}$ , and  $R_o$ . Also, if a load resistance of  $10 \text{ k}\Omega$  is connected to the output, what overall voltage gain  $G_V$  is realized? Now, if a 0.5-V peak sine-wave signal is required at the output, what must the peak amplitude of  $v_{sig}$  be?



### Exercise 4. (20pt)

Design the circuit of **Fig.P4** for a MOSFET having  $V_t = 0.6 \text{ V}$  and  $k_n = 5 \text{ mA/V}^2$ . Let  $V_{DD} = V_{SS} = 3 \text{ V}$ . Design for a dc bias current of  $0.4 \text{ mA}$  and for the largest possible voltage gain (and thus the largest possible  $R_D$ ) consistent with allowing a  $1.2\text{-V}$  peak-to-peak voltage swing at the drain. Assume that the signal voltage on the source terminal of the FET is zero.



**Fig.P4**

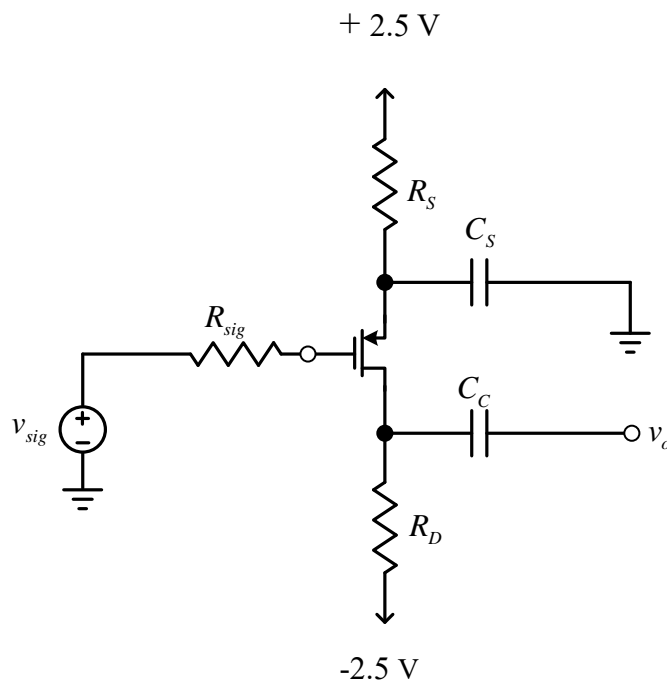
### Exercise 5. (20pt)

Note: This question requires simulation. Please note that you need to use **Multisim** for simulation and provide the simulation circuit and simulation results in your answer.

Ensure that you provide both **theoretical calculation** results and **simulation** results.

The PMOS transistor in the CS amplifier of **Fig.P6** has  $V_{tp} = -0.75\text{ V}$  and a very large  $|V_A|$ .

- (a) Select a value for  $R_S$  to bias the transistor at  $I_D = 0.5\text{ mA}$  and  $|V_{ov}| = 0.25\text{ V}$ . Assume  $v_{sig}$  to have a zero dc component.
- (b) Select a value for  $R_D$  that results in  $G_v = -12\text{ V/V}$ .



**Fig.P5**